

FILM FORMING METHOD OF OXIDE SUPERCONDUCTOR

FILM FORMING METHOD OF OXIDE SUPERCONDUCTOR

Patent Number: JP7070752
Publication date: 1995-03-14
Inventor(s): MATSUBARA MASAHIKO; others: 02
Applicant(s): KOKUSAI CHODENDO SANGYO GIJUTSU KENKYU CENTER; others: 02
Requested Patent: JP7070752
Application Number: JP19930217266 19930901
Priority Number(s):
IPC Classification: C23C16/40; H01B1/08; H01B12/06; H01B13/00
EC Classification:
EC Classification:
Equivalents:

Abstract

PURPOSE: To improve the smoothness of a film and improve crystallizability in the atomic layer epitaxy film forming.

CONSTITUTION: In the film forming method of the oxide superconductor forming the atomic layer epitaxy film of the oxide superconductor consisting of the compd. containing more than three component metal element, the process in which plural metal elements consisting of one part of an unit lattice is laminated simultaneously as one unit is included. In the film forming method of $RBa_2 Cu_3O_7-\delta$ (R is either one among Y, La, Pr, Nd, Sm, Eu, Gd, Dy, Ho, Er and Yb), the simultaneously laminating process of Cu, R and Cu as a subunit in order of Ba/Cu, R and Cu/Ba/Cu is included.